

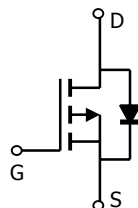
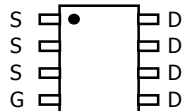
4401**P-Channel Enhancement Mode Field Effect Transistor****General Description**

The AO4401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

Features

V_{DS} (V) = -30V
 I_D = -6.1 A
 $R_{DS(ON)} < 46m\Omega$ ($V_{GS} = -10V$)
 $R_{DS(ON)} < 61m\Omega$ ($V_{GS} = -4.5V$)
 $R_{DS(ON)} < 117m\Omega$ ($V_{GS} = -2.5V$)

SOIC-8
Top View

**Absolute Maximum Ratings** $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current ^A	$T_A=25^\circ\text{C}$	I_D	-6.1	A
	$T_A=70^\circ\text{C}$		-5.1	
Pulsed Drain Current ^B		I_{DM}	-60	
Power Dissipation ^A	$T_A=25^\circ\text{C}$	P_D	3	W
	$T_A=70^\circ\text{C}$		2.1	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10s$	$R_{\theta JA}$	31	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	Steady-State		59	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	16	24	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 12\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-0.7	-1	-1.3	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-4.5\text{V}$, $V_{DS}=-5\text{V}$				A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-6.1\text{A}$ $T_J=125^{\circ}\text{C}$		38	46	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-5\text{A}$		49	61	$\text{m}\Omega$
		$V_{GS}=-2.5\text{V}$, $I_D=-1\text{A}$		76	117	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-5\text{A}$	7	11		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.75	-1	V
I_S	Maximum Body-Diode Continuous Current				-4.2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		940		pF
C_{oss}	Output Capacitance			104		pF
C_{rss}	Reverse Transfer Capacitance			73		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		6		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	$V_{GS}=-4.5\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-5\text{A}$		9.4		nC
Q_{gs}	Gate Source Charge			2		nC
Q_{gd}	Gate Drain Charge			3		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=2.4\Omega$, $R_{GEN}=6\Omega$		7.6		ns
t_r	Turn-On Rise Time			8.6		ns
$t_{D(off)}$	Turn-Off DelayTime			44.7		ns
t_f	Turn-Off Fall Time			16.5		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		22.7		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-5\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		15.9		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any a given application depends on the user's specific board design. The current rating is based on the $t_s \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

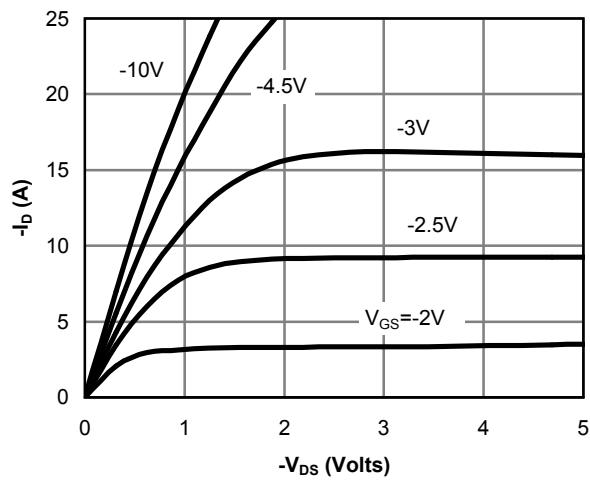


Fig 1: On-Region Characteristics

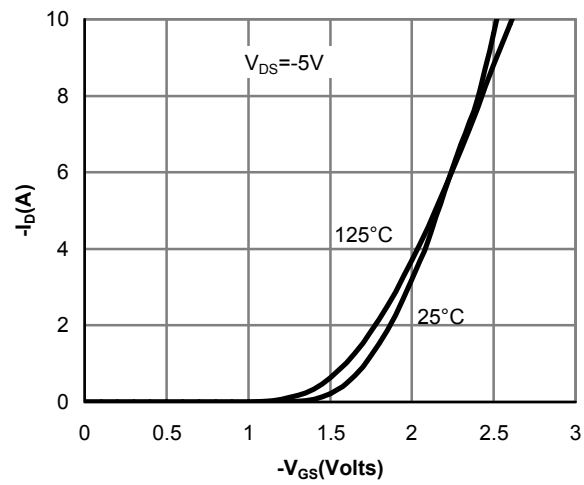


Figure 2: Transfer Characteristics

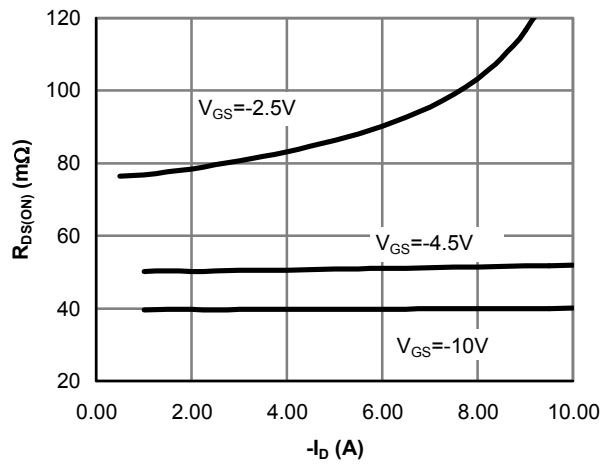


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

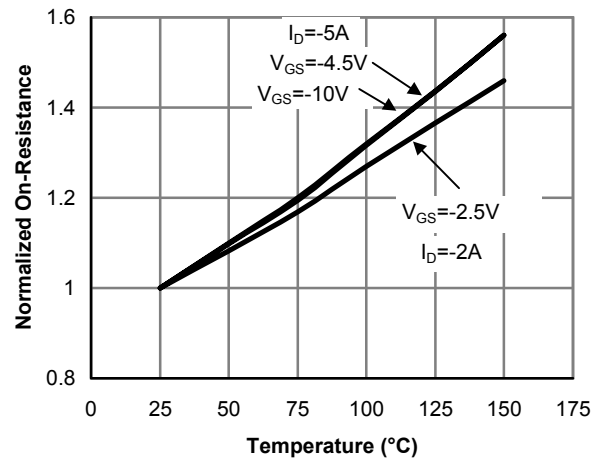


Figure 4: On-Resistance vs. Junction Temperature

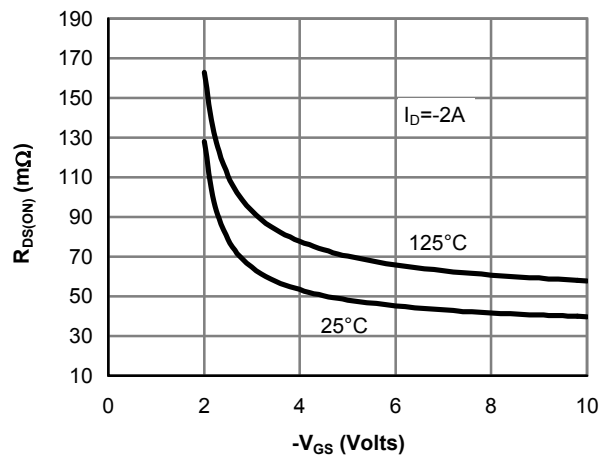


Figure 5: On-Resistance vs. Gate-Source Voltage

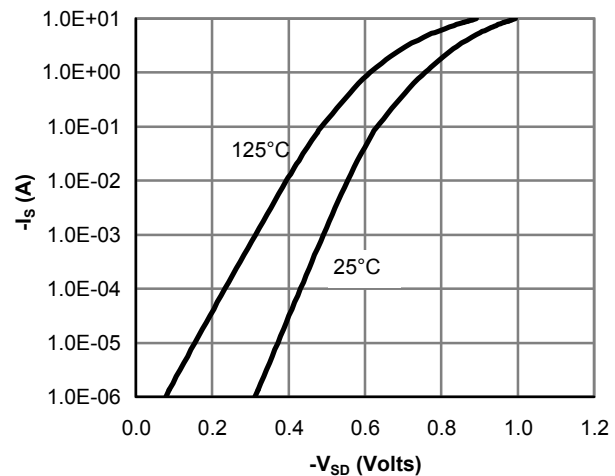


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

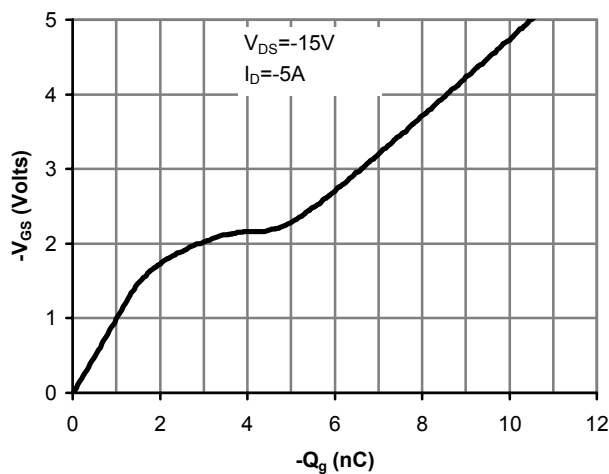


Figure 7: Gate-Charge Characteristics

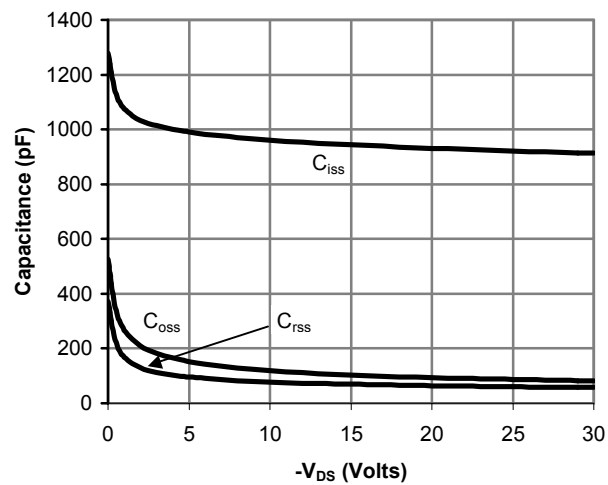


Figure 8: Capacitance Characteristics

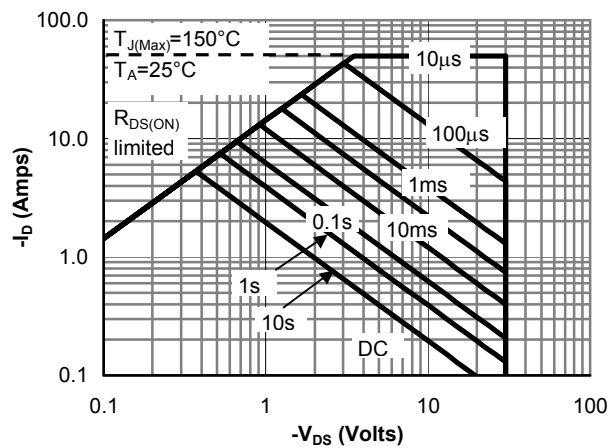


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

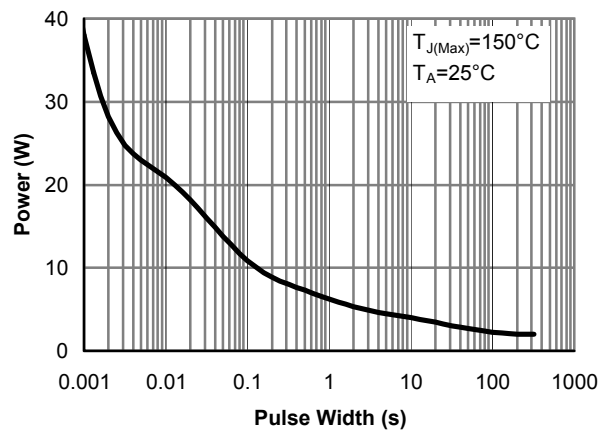


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

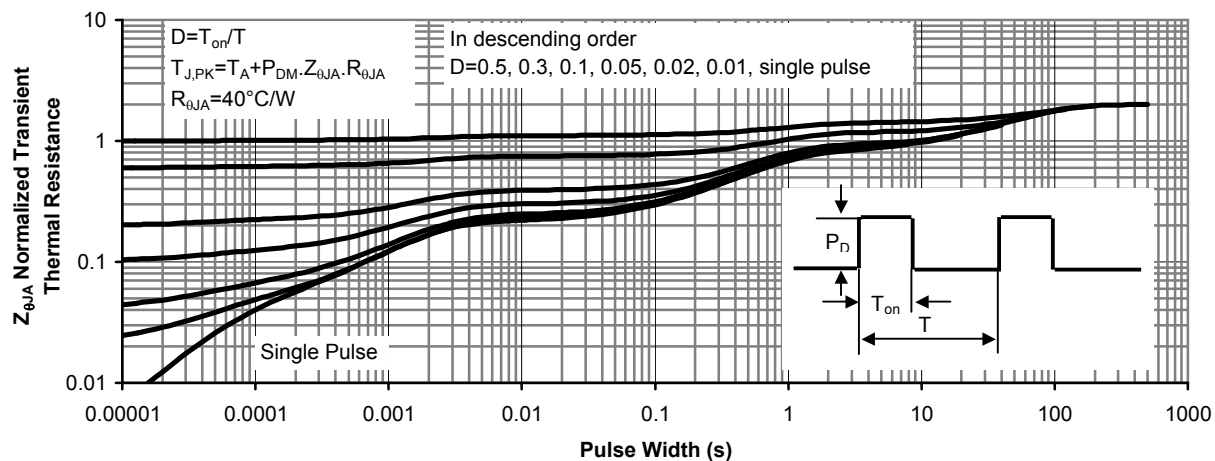


Figure 11: Normalized Maximum Transient Thermal Impedance